

Chip Specification

General Description:

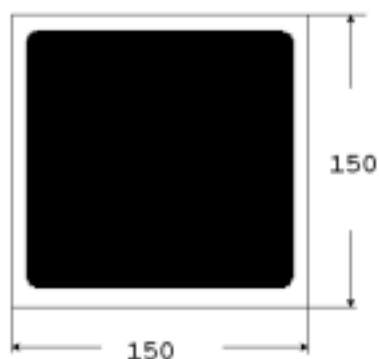
Schottky Diode chips with Mo-barrier for switch mode power rectifiers with the following features:

- * **Guard-ring for stress protection**
- * **Extremely low forward voltage**
- * **125 °C operation junction temperature**
- * **reverse avalanche behavior**

Mechanical Data:

MBR3045 passivated Silicon Chip

Demension(mil)	150x150
Thickness:	350 +- 20 μ m
Metallization:	
Top (Anode) :	Al Ag
Bottom (Cathode) :	TiNiAg



Forward Current(A)	30A
Reverse Voltage (V):	>45V

Type	Chip	VF(V)@25 C	VF(V)@125 C	I_{RM} @ V_{RMM}
	size(mil)	at If=30A	at If=30A	at 25 C
MBR3045	150x150	0,54V	0,47V	0,6mA

* expected value for recommended assembling with both side soldering
 Typical devise MBR3045

Note: Other voltages & Top Metal AL are available

